

# Gunter Semiconductor GmbH

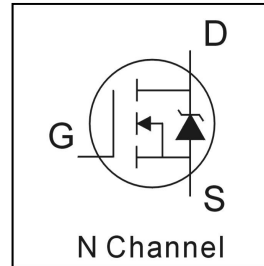
# GFC450

## N Channel Power MOSFET

## Chip Specification

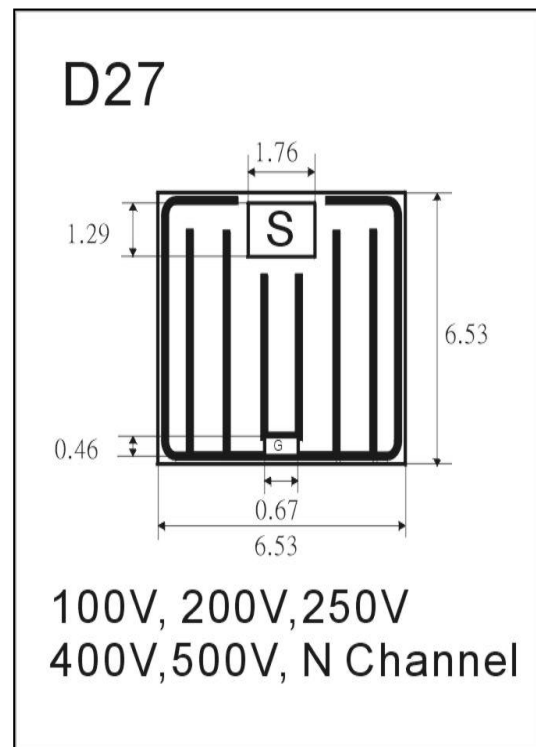
### General Description:

- \* Advanced Process Technology
- \* Dynamic dV/dt Rating
- \* **150°C Operating Temperature**
- \* **Fast Switching**
- \* **Fully Avalanche Rated**



### Mechanical Data:

D27	
Dimension	6.53mm x 6.53mm
Thickness:	400 μm
Metallization:	
Top :	Al
Backside :	CrNiAg / Au
Suggested Bonding Conditions:	
Die Mounting:	Solder Perform
	95/5 PbSn or 92.5/2.5/5 PbAgIn
Source Bonding Wire:	20 mil Al



### Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	500	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.4	Ω	VGS=10V, ID=8.4A
Continuous Drain current ( in target package)	ID@25°C	14	A	VGS=10V
Continuous Drain current ( in target package)	ID@100°C	8.7	A	VGS=10V
Operation Junction	Tj	-55~150	°C	
Storage Temperature	TSTR	-55~150	°C	

### Target Device: IRFP450

TO-247AC

Pd

190

W

@Tc=25°C

